	Тур	Hi ts	Search Text	DBs	Time Stamp	ı	r D e f	r o r
1	IS& R	3	("6600137").PN	USPAT; US-PGPUB; EPO; JPO; DERWENT;	2004/07/21 12:47			0
2	IS& R	2	("6056191").PN	世 <b>8坪A</b> 平 <b>D</b> B US-PGPUB; EPO; JPO; DERWENT;	2004/07/21 12:47			0
3	IS& R	2	("5601229").PN	世 <b>8坪<u>A</u>平</b> DB US-PGPUB; EPO; JPO; DERWENT;	2004/07/21 12:48			0
4	IS& R	2	("6034578").PN	世 <b>8坪A</b> 平 <b>D</b> B US-PGPUB; EPO; JPO; DERWENT;	2004/07/21 12:50			0
5	BRS	17 67	charge with (neutral\$6 or remov\$6) with semiconductor	<b>世島学<u>A</u>早</b> 身B US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/07/21 12:51			0
6	BRS	14 1	charge with (neutral\$6 or remov\$6) with semiconductor same apparatus	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/07/21 12:51			0
7	BRS	11 4	charge with (neutral\$6 or remov\$6) with semiconductor with apparatus	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/07/21 12:53			0
8	BRS		-	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/07/21 12:53			0
9	BRS		charge with (neutral\$6 or remov\$6) with semiconductor with apparatus and heat\$6 and cool\$6	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/07/21 12:58			0

	Тур	Hi ts	Search Text	DBs	Time Stamp	m m e	r D e f	r r o r
10	BRS	14	charge with (neutral\$6 or remov\$6) same semiconductor same heat\$6 same cool\$6	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/07/21 13:11			0
11	BRS	3	3620850.URPN.	USPAT	2004/07/21 13:09			0
12	BRS	22		USPAT; US-PGPUB; EPO; JPO; DERWENT;	2004/07/21 13:56	*		Ο
13	BRS	2	(rear or	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/07/21 13:58			0
14	BRS	5		USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/07/21 13:58			0
15	BRS		charge with (neutrali\$6 or remov\$6) with (rear or backside) with (heat\$6 or cool\$6)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/07/21 14:51			0

	Тур	Hi ts	Search Text	DBs	Time Stamp	m m e	r D e f i	Errors
16	BRS	1		US-PGPUB; EPO; JPO; DERWENT;	2004/07/21 14:53			0
17	BRS	1	(\$8static or piezo\$8) with charge with (neutrali\$6 or remov\$6) with (rear or backside) with (heat\$6 or cool\$6) and semiconductor	US-PGPUB; EPO; JPO; DERWENT;	2004/07/21 14:55			0
18	BRS	5		US-PGPUB; EPO; JPO; DERWENT;	2004/07/21 14:58			0
19	BRS	21 7	backside) with (heat\$6 or		2004/07/21 16:24			0

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	Тур	Hi ts	Search Text	DBs	Time Stamp	m m e	r D e f i	Error
20	BRS	93		USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/07/21 15:00			О
21	BRS	29		USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/07/21 15:10			О
22	BRS	1	charge near (neutrali\$6 or remov\$6) and (rear or backside) near (heat\$6 or cool\$6 or temperature) and charge with temperature and semiconduc	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/07/21 15:12			Ο

	Тур	Hi ts	Search Text	DBs	Time Stamp	m e	D e f	
23	BRS	2	l .	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/07/21 15:17			0
24	BRS	84	charge near appearance	USPAT; US-PGPUB; EPO; JPO; DERWENT;	2004/07/21 15:55			0
25	BRS	21	charge near appearance and semiconductor	JPO; DERWENT;	2004/07/21 15:45			0
26	BRS		charge near appearance with (remov\$6 or neutrali\$6) and cool\$6 and heat\$6 and semiconductor	IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/07/21 15:47			0
27	BRS	1	charge near appearance with cool\$6 and	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/07/21 15:46			0
28	BRS	66		USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/07/21 15:48		***************************************	0

	Тур	Hi ts	Search Text	DBs	Time Stamp	C o m m e n t s	e	r o r
29	BRS	3	charge with (remov\$6 or neutrali\$6) and cool\$6 and heat\$6 and semiconductor and charge near	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/07/21 15:54			0
30	BRS	1	engrgeanear appearance with	USPAT; US-PGPUB; EPO; JPO; DERWENT;	2004/07/21 15:56			0
31	BRS	19 13	semiconductor charge near semiconductor	世 <b>5</b> 坪A〒PB US-PGPUB; EPO; JPO; DERWENT;	2004/07/21 15:56			0
32	BRS	23	remov\$6 near charge near semiconductor	世島姓 <u>入</u> 丁身B US-PGPUB; EPO; JPO; DERWENT;	2004/07/21 15:56			0
33	BRS	4	remov\$6 near charge near semiconductor and (heat\$6 or cool\$6)	IBM TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/07/21 16:04			0
34	BRS	1	1998-386116.NR AN.	DERWENT	2004/07/21 16:02			0
35	BRS	10 34 9	narita .inv.	USPAT; US-PGPUB; EPO; JPO; DERWENT;	2004/07/21 16:04			0
36	BRS	9	narita .inv. and charge	世島峰五甲身B US-PGPUB; EPO; JPO; DERWENT;	2004/07/21 16:05			0
37	BRS	23	narita .inv. and charge with remov\$6	<b>世島坪<u>A</u>甲</b> PB US-PGPUB; EPO; JPO; DERWENT;	2004/07/21 16:08			0
38	BRS	13 14 4	narita shoriki .inv. and charge with remov\$6	JPO; DERWENT; IBM_TDB	2004/07/21 16:08			0
39	BRS	i	narita .inv. and shoriki and charge with remov\$6	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/07/21 16:09			0

	Тур	Hi ts	Search Text	DBs	Time Stamp	m m e n	r D e f i	i 1
40	BRS	44	charge with (neutrali\$6 or remov\$6) and (rear or backside) with heat\$6 and (rear or backside) with cool\$6 and temperature with control\$6 and semiconductor	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/07/21 16:40			0
41	BRS		charge near (neutrali\$6 or remov\$6) and (rear or backside) with heat\$6 and (rear or backside) with cool\$6 and temperature with control\$6 and semiconductor	US-PGPUB; EPO;	2004/07/21 16:37			0
42	BRS	2	(rear or backside) with cool\$6 and temperature with control\$6 and semiconductor	JPO; DERWENT; IBM_TDB	2004/07/21 16:39			0
43	IS& R	2		:   \ =    -	2004/07/21 16:39			0

	Тур	Hi ts	Search Text	DBs	Time Stamp	m m e	D	Enrons
44	BRS		charge with remov\$6 and (rear or backside) with heat\$6 and (rear or backside) with cool\$6 and temperature with control\$6 and semiconductor	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/07/21 16:41			0
45	BRS	0.1	backside) with	USPAT; US-PGPUB; EPO;	2004/07/22 15:53			0
46	BRS	13 15	charge with remov\$6 with semiconductor	JPO; DERWENT;	2004/07/22 15:53			0
47	BRS	1	charge with remov\$6 with semiconductor and (rear or backside) with heat\$6 and (rear or backside) with cool\$6 and temperature near control\$6		2004/07/22 15:55			0

	Тур	Hi ts	Search Text	DBs	Time Stamp	m m e	r D e f i n	Errors
48	BRS	1	charge near remov\$6 with semiconductor and (rear or backside) with heat\$6 and (rear or backside) with cool\$6 and temperature near control\$6	1	2004/07/22 15:55			Ο
49	BRS	3	charge near remov\$6 with semiconductor and heat\$6 and cool\$6 and temperature near control\$6		2004/07/22 15:57			0
50	BRS	18	charge with remov\$6 with semiconductor and heat\$6 and cool\$6 and temperature near control\$6	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/07/22 21:32			0
51	BRS	2	charge with remov\$6 and pyro and electric\$6 and heat\$6 and cool\$6 and temperature near control\$6	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/07/22 21:38			0
52	BRS	8	charge with remov\$6 and pyro adj electric\$6	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/07/22 21:41			0
53	BRS	11	remov\$6 with pyro adj electric\$6	USPAT; US-PGPUB; EPO; JPO; DERWENT;	2004/07/22 21:50			0
54	BRS	0	1077111.URPN.	IBM TDB USPAT	2004/07/22 21:48			0

	Тур	Hi ts	Search Text	DBs	Time Stamp	m m e	r D e f i	E r r
55	BRS	16 49	charge with (semiconductor or wafer)		2004/07/22 21:50		***************************************	0
56	BRS	8	remov\$6 with charge with (semiconductor or wafer) and pyroelectric	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/07/22 22:03			0
57	BRS	1	2002-612829.NR AN.	DERWENT	2004/07/22 22:01			0
58	BRS	1	2001-138194.NR AN.	DERWENT	2004/07/22 22:01			0
59	BRS	29	remov\$6 with charge with (semiconductor or wafer) and (pyroelectric or piezoelectric)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/07/22 22:18			0
60	BRS	21	remov\$6 with charge with (semiconductor or wafer or substrate) and pyroelectric	JPO; DERWENT;	2004/07/22 22:32			0
61	BRS	1	2002-612829.NR AN.	DERWENT	2004/07/22 22:25			0
62	BRS	78	remov\$6 with charge with (semiconductor or wafer or substrate) and (pyroelectric or piezoelectric) and (heat\$6 or cool\$6 or temperature)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/07/22 22:33			0

	Тур	Hi ts	Search Text	DBs	Time Stamp	m m e n t	r D e f	E r o r
63	BRS	8	or	1	2004/07/22 22:34			Ο
64	BRS	23	(pyroelectric or piezoelectric) and (heat\$6 or cool\$6 or temperature)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/07/22 22:43			0
65	BRS		remov\$6 near charge near (semiconductor or wafer or substrate) and (heat\$6 or cool\$6 or temperature) near (semiconductor or wafer or substrate)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/07/22 23:04			0

	Тур	Hi ts	Search Text	DBs	Time Stamp	m e n	r D e f i n	Error
66	BRS	3			2004/07/22 23:05			0
67	BRS	12	substrate)	-	2004/07/22 23:33			0
68	IS& R	2	("5341979").PN	USPAT; US-PGPUB; EPO; JPO; DERWENT;	2004/07/22 23:33			0
69	BRS	1	2002-366356.NR AN.	IBM TDB DERWENT	2004/07/23 00:48			0
70	BRS	1	2002-366356.NR AN.	DERWENT	2004/07/23 00:52			0